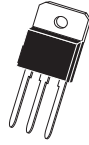


TIP140 TIP141 TIP142 NPN  
TIP145 TIP146 TIP147 PNP

**SILICON POWER DARLINGTON  
COMPLEMENTARY TRANSISTORS**



**TO-218 TRANSISTOR CASE**

**MAXIMUM RATINGS: ( $T_C=25^\circ\text{C}$ )**

Collector-Base Voltage	$V_{CBO}$	60	80	100	V
Collector-Emitter Voltage	$V_{CEO}$	60	80	100	V
Emitter-Base Voltage	$V_{EBO}$		5.0		V
Continuous Collector Current	$I_C$		10		A
Peak Collector Current	$I_{CM}$		20		A
Base Current	$I_B$		0.5		A
Power Dissipation	$P_D$		125		W
Operating and Storage Junction Temperature	$T_J, T_{stg}$		-65 to +150		$^\circ\text{C}$
Thermal Resistance	$\Theta_{JC}$		1.0		$^\circ\text{C/W}$

**ELECTRICAL CHARACTERISTICS: ( $T_C=25^\circ\text{C}$  unless otherwise noted)**

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
$I_{CBO}$	$V_{CB}=\text{Rated } V_{CBO}$			1.0	mA
$I_{CEO}$	$V_{CE}=\frac{1}{2} \text{ Rated } V_{CEO}$			2.0	mA
$I_{EBO}$	$V_{EB}=5.0\text{V}$			2.0	mA
$BV_{CEO}$	$I_C=30\text{mA}$ (TIP140, TIP145)	60			V
$BV_{CEO}$	$I_C=30\text{mA}$ (TIP141, TIP146)	80			V
$BV_{CEO}$	$I_C=30\text{mA}$ (TIP142, TIP147)	100			V
$V_{CE(SAT)}$	$I_C=5.0\text{A}, I_B=10\text{mA}$			2.0	V
$V_{CE(SAT)}$	$I_C=10\text{A}, I_B=40\text{mA}$			3.0	V
$V_{BE(ON)}$	$V_{CE}=4.0\text{V}, I_C=10\text{A}$			3.0	V
$V_F$	$I_F=10\text{A}$			2.8	V
$h_{FE}$	$V_{CE}=4.0\text{V}, I_C=5.0\text{A}$	1000			
$h_{FE}$	$V_{CE}=4.0\text{V}, I_C=10\text{A}$	500			
$t_{on}$	$I_C=10\text{A}, I_{B1}=I_{B2}=40\text{mA}, R_L=3.0\Omega$		0.9		$\mu\text{s}$
$t_{off}$	$I_C=10\text{A}, I_{B1}=I_{B2}=40\text{mA}, R_L=3.0\Omega$		4.0		$\mu\text{s}$

R2 (1-August 2008)

# Central<sup>TM</sup>

**Semiconductor Corp.**

**DESCRIPTION:**

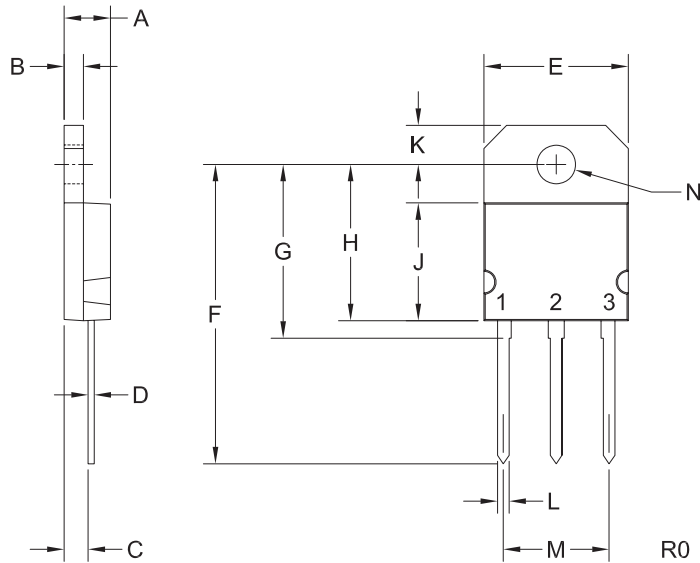
The CENTRAL SEMICONDUCTOR TIP140, TIP145 series types are Complementary Silicon Power Darlington Transistors manufactured by the epitaxial base process, designed for general purpose amplifier and low speed switching applications where high gain is required.

**MARKING: FULL PART NUMBER**

	TIP140	TIP141	TIP142	
SYMBOL	TIP145	TIP146	TIP147	UNITS
$V_{CBO}$	60	80	100	V
$V_{CEO}$	60	80	100	V
$V_{EBO}$		5.0		V
$I_C$		10		A
$I_{CM}$		20		A
$I_B$		0.5		A
$P_D$		125		W
$T_J, T_{stg}$		-65 to +150		$^\circ\text{C}$
$\Theta_{JC}$		1.0		$^\circ\text{C/W}$

**SILICON POWER DARLINGTON  
COMPLEMENTARY TRANSISTORS**

**TO-218 TRANSISTOR CASE - MECHANICAL OUTLINE**



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.185	0.193	4.70	4.90
B	0.075	0.082	1.91	2.08
C	0.098		2.49	
D	0.019	0.030	0.48	0.76
E	0.578	0.598	14.68	15.19
F	1.220		30.99	
G	0.708		17.98	
H	-	0.637	-	16.18
J	-	0.480	-	12.19
K	0.155	0.163	3.94	4.14
L	0.043	0.051	1.09	1.30
M	0.425	0.437	10.80	11.10
N	0.157	0.161	3.99	4.09

TO-218 Transistor (REV: R0)

**LEAD CODE:**

- 1) BASE
- 2) COLLECTOR
- 3) EMITTER

Note: Tab is common to lead 2.

**MARKING:**

**FULL PART NUMBER**